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10/008,683**Information Disclosure Statement
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(Use several sheets if necessary)

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Applicant
Chris E. Barns et al.Filing Date
December 4, 2001Group Art Unit
1765**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AB							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
<i>jd</i>	AC	Ducroquet et al., "Full CMP Integration...", IEEE Transactions on Electron Devices, 48(8):1816-1821, 2001
	AD	Matsuda et al., "Performance Improvement of Metal...", Symposium on VLSI Technology Digest of Technical Papers, 2001
	AE	Ushiki et al., "Reliable Tantalum-Gate...", IEEE Transactions on Electron Devices, 44(9):1467-1472, 1997
	AF	Yagishita et al., "Improvement of Threshold Voltage...", IEEE Transactions on Electron Devices, 48(8):1604-1611, 2001
	AG	Planar Solutions Announces New Second Step Copper CMP Slurry," Arch SemiConductor Photopolymers: About Us
	AH	Conaghan et al., "Applications of silicides in semiconductor processing,"
	AI	Abstract, Cabot Microelectronics Corporation, Semiconductor Products, 2000
<i>jd</i>	AJ	Abstract, Cabot Microelectronics Corporation, FAX (Frequently Asked Questions), 2000

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EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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